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VNI4140K-32 Pin connection

1 Pin connection

Figure 2. Pin connection (top view)

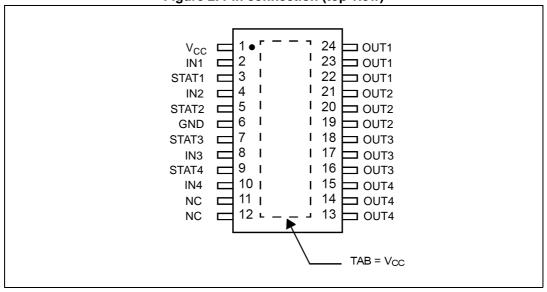


Table 1. Pin description

Pin	Name	Description
Tab	TAB	Exposed tab internally connected to V _{cc}
1	V _{CC}	Supply voltage
2	IN1	Channel 1 input 3.3 V CMOS/TTL compatible
3	STAT1	Channel 1 status in open drain configuration
4	IN2	Channel 2 input 3.3 V CMOS/TTL compatible
5	STA2	Channel 2 status in open drain configuration
6	GND	Device ground connection
7	STAT3	Channel 3 status in open drain configuration
8	IN3	Channel 3 input 3.3 V CMOS/TTL compatible
9	STAT4	Channel 4 status in open drain configuration
10	IN4	Channel 4 input 3.3 V CMOS/TTL compatible
11	NC	
12	NC	
13	OUT4	Channel 4 power stage output, internally protected
14	OUT4	Channel 4 power stage output, internally protected
15	OUT4	Channel 4 power stage output, internally protected
16	OUT3	Channel 3 power stage output, internally protected
17	OUT3	Channel 3 power stage output, internally protected



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Pin connection VNI4140K-32

Table 1. Pin description (continued)

Pin	Name	Description
18	OUT3	Channel 3 power stage output, internally protected
19	OUT2	Channel 2 power stage output, internally protected
20	OUT2	Channel 2 power stage output, internally protected
21	OUT2	Channel 2 power stage output, internally protected
22	OUT1	Channel 1 power stage output, internally protected
23	OUT1	Channel 1 power stage output, internally protected
24	OUT1	Channel 1 power stage output, internally protected

VNI4140K-32 Maximum ratings

2 Maximum ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CC}	Power supply voltage	41	V
-V _{CC}	Reverse supply voltage	-0.3	V
I _{GND}	DC ground reverse current	-250	mA
I _{OUT}	Output current (continuous)	Internally limited	Α
I _R	Reverse output current (per channel)	-5	Α
I _{IN}	Input current (per channel)	± 10	mA
V _{IN}	Input voltage	+V _{CC}	V
V _{STAT}	Status pin voltage	+V _{CC}	V
I _{STAT}	Status pin current	± 10	mA
V _{ESD}	Electrostatic discharge (R = 1.5 k Ω ; C = 100 pF)	2000	V
E _{AS}	I _{OUT} = 500 mA T _{AMB} = 125 °C	5	J
P _{TOT}	Power dissipation at T _c = 25 °C	Internally limited	W
TJ	Junction operating temperature	Internally limited	°C
T _{STG}	Storage temperature	-55 to 150	°C

2.1 Thermal data

Table 3. Thermal data

Symbol	Parameter		Value	Unit
R _{th(JC)}	Thermal resistance junction-case ⁽¹⁾	Max.	2	°C/W
R _{th(JA)}	Thermal resistance junction-ambient	Max.	see Figure 11	°C/W

^{1.} Per channel.

3 Recommended

Table 4. Input switching limits

Symbol	Parameter	Value	Unit
f _{Vin MAX}	Maximum input switching frequency	10	kHz

Electrical characteristics VNI4140K-32

4 Electrical characteristics

10.5 V < V_{CC} < 36 V; -40 °C < T_{J} < 125 °C; unless otherwise specified.

Table 5. Power section

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{cc}	Supply voltage		10.5		36	V
R _{DS(on)}	ON state resistance	I_{OUT} = 0.7 A at T_J = 25 °C I_{OUT} = 0.7 A			0.080 0.140	Ω
V _{clamp}		I _s = 20 mA	41	45	52	V
I _S	Supply current	All channels in OFF state, ON state with V _{IN} = 5 V		250 2.4	4	μA mA
V _{OUT(OFF)}	OFF state output voltage	V _{IN} = 0 V and I _{OUT} = 0 A			1	V
I _{OUT(OFF)}	OFF state output current	V _{IN} = V _{OUT} = 0 V	0		5	μА
I _{LGND}	Output current in ground disconnection	$V_{CC} = V_{IN} = GND = 24 V;$ $T_J = 125 °C$			500	μΑ
F _{CP}	Charge pump frequency	Channel in ON state ⁽¹⁾		1450		kHz

^{1.} To cover EN55022 class A and class B normative.

 V_{CC} = 24 V; -40 °C < T_{J} < 125 °C, R_{L} = 48 $\Omega,$ input rise time < 0.1 μs

Table 6. Switching

Symbol	Parameter	Min.	Тур.	Max.	Unit
t _{d(ON)}	Turn ON delay	-	6	-	μs
t _r	Rise time	-	5	-	μs
t _d (OFF)	Turn OFF	-	12	-	μs
t _f	Fall time	-	5	-	μs
dV/dt _(ON)	Turn ON voltage slope	-	4	-	V/µs
dV/dt(_{OFF})	Turn OFF voltage slope	-	4	-	V/µs

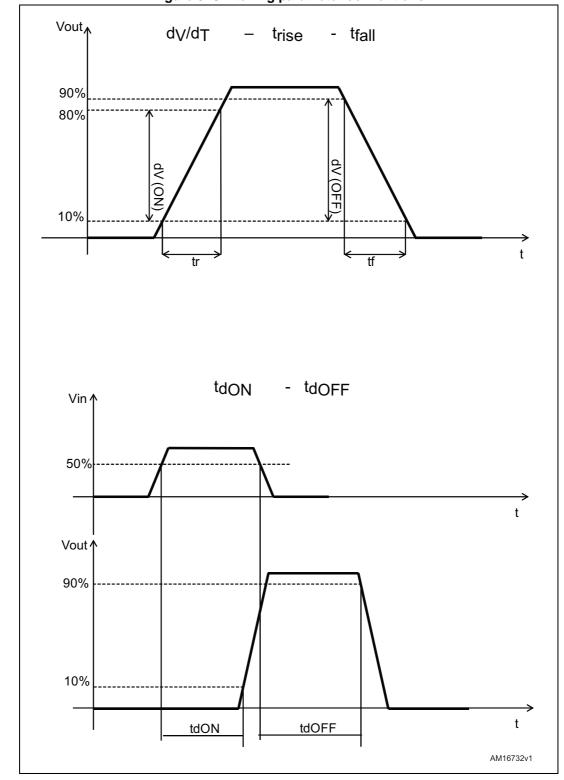


Figure 3. Switching parameter conventions

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Electrical characteristics VNI4140K-32

Table 7. Logical input

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{IL}	Input low level voltage				0.8	V
V _{IH}	Input high level voltage		2.20			V
V _{I(HYST)}	Input hysteresis voltage			0.15		V
	Input current	V _{IN} = 15 V			10	^
I _{IN}	Input current	V _{IN} = 36 V			210	μΑ

Table 8. Protection and diagnostic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{STAT}	Status voltage output low	I _{STAT} = 1.6 mA			0.6	V
V _{USD}	Undervoltage protection		7		10.5	٧
V _{USDHYS}	Undervoltage hysteresis		0.4	0.5		٧
I _{LIM}	DC short-circuit current	$V_{CC} = 24 \text{ V}; R_{LOAD} < 10 \text{ m}\Omega$	1.1		2.6	Α
I _{PEAK}	Maximum DC output current	Dynamic load		1.6		А
I _{LSTAT}	Status leakage current	V _{CC} = V _{STAT} = 36 V		30		μА
T _{TSD}	Junction shutdown temperature		150	170	190	°C
T _R	Junction reset temperature		135			°C
T _{HIST}	Junction thermal hysteresis		7	15		°C
T _{CSD}	Case shutdown temperature		125	130	135	ů
T _{CR}	Case reset temperature		110			°C
T _{CHYST}	Case thermal hysteresis		7	15		°C
V _{demag}	Output voltage at turn-OFF	I _{OUT} = 0.5 A; L _{LOAD} >= 1 mH	V _{CC} -41	V _{CC} -45	V _{CC} -52	V

VNI4140K-32 Electrical characteristics

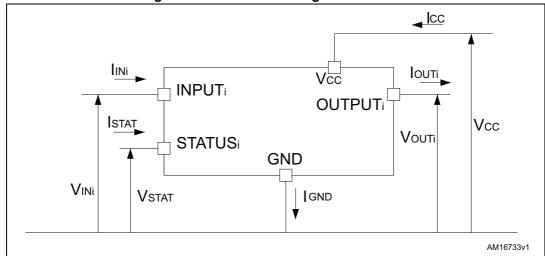


Figure 4. Current and voltage conventions



Truth table VNI4140K-32

5 Truth table

Table 9. Truth table

Conditions	INPUTn	OUTPUTn	STATUSn
Normal operation	L	L	H
	H	H	H
Overtemperature	L	L	H
	H	L	L
Undervoltage	L	L	X
	H	L	X
Shorted load (current limitation before thermal shutdown)	L	L	H
	H	X	H

6 Thermal management

The power dissipation in the IC is the main factor that sets the safe operating condition of the device in the application. Therefore, it must be considered very carefully. Furthermore, the available space on the PCB should be chosen considering the power dissipation. Heat sinking can be achieved using copper on the PCB with proper area and thickness. Two different protections have been implemented to guarantee safety of the device if it overheats due to an overloaded condition or high environment temperature. The following flowchart explains in detail this protection functionality.

Vin(i) = HOUT(i) On STAT(i) Off (H) NO YES Tj(i) > TtsdOUT(i) Off STAT(i) On (L) YES NO Tc > Tcsd YES NO Tc > Tcr NO YES Tj(i) > Tjr

Figure 5. Thermal behavior

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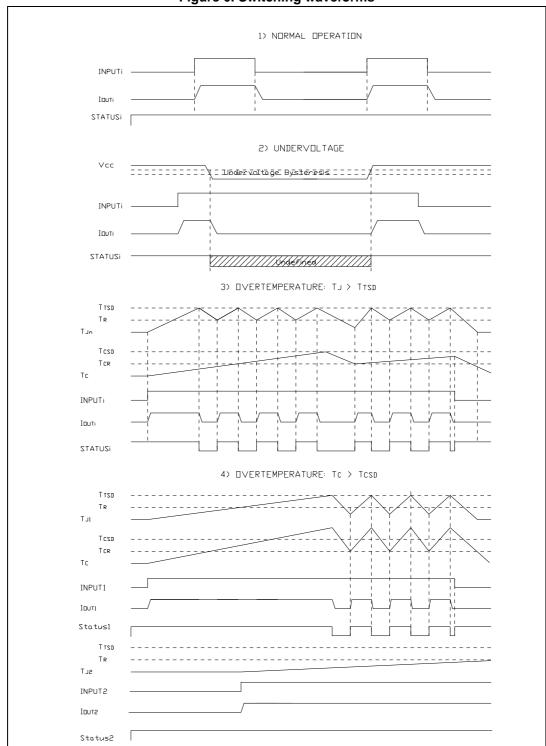
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Switching waveforms VNI4140K-32

7 Switching waveforms





VNI4140K-32 Pin functions

8 Pin functions

Figure 7. Input circuit

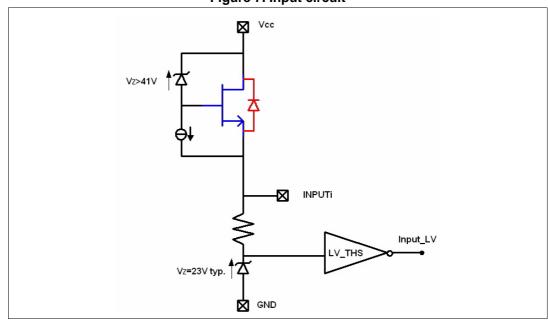
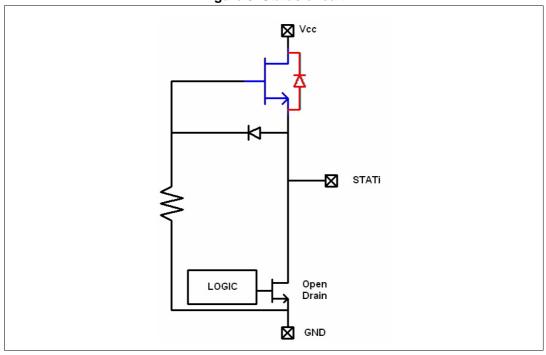


Figure 8. Status circuit



Pin functions VNI4140K-32

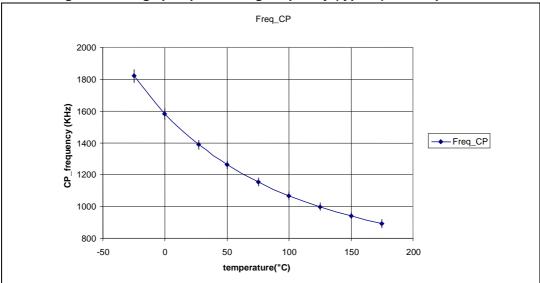
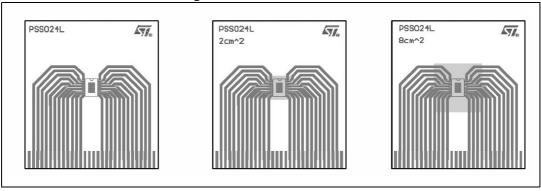


Figure 9. Charge pump switching frequency (typical) vs. temperature

9 Package and PCB thermal data

9.1 VNI4140K-32 thermal data

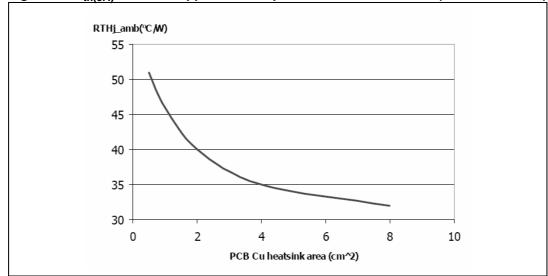
Figure 10. VNI4140K-32 PCB



Note:

Layout condition of R_{th} and Z_{th} measurements (PCB: double layer, thermal vias, FR4 area = 77 mm x 86 mm, PCB thickness=1.6 mm, Cu thickness = 70 mm (front and back side), copper areas: from minimum pad layout to 8 cm²).

Figure 11. R_{th(JA)} vs. PCB copper area in open box free air condition (one channel ON)



ZTH (°C,W) 1000 Footprint 100 2 cm² 8 cm² 10 0.1 0.0001 0.001 1000 0.01 0.1 1 10 100 Time (s)

Figure 12. VNI4140K-32 thermal impedance junction-ambient single pulse (one channel ON)

Reverse polarity protection 10

Reverse polarity protection can be implemented on board using two different solutions:

- Placing a resistor (R_{GND}) between IC GND pin and load GND
- Placing a diode between IC GND pin and load GND 2.

If option 1 is selected, the minimum resistance value has to be selected according to the following equation:

Equation 1

where I_{GND} is the DC reverse ground pin current and can be found in Section 2: Maximum ratings of this datasheet.

Power dissipated by R_{GND} (when $V_{CC} < 0$: during reverse polarity situations) is:

Equation 2

$$P_D = V_{CC}^2 / R_{GND}$$

If option 2 is selected, the diode has to be chosen by taking into account VRRM > |V_{cc}| and its power dissipation capability:

Equation 3

$$P_D \ge I_S^*V_F$$

Note:

In normal conditions (no reverse polarity), due to the diode, there is a voltage drop between GND of the device and GND of the system.

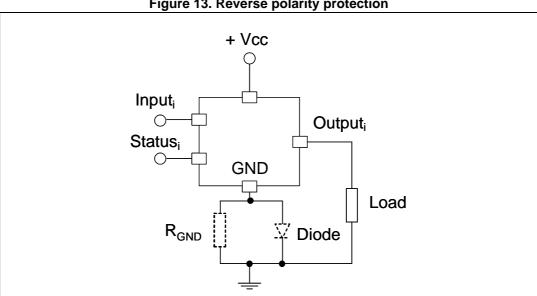


Figure 13. Reverse polarity protection

This schematic can be used with any type of load.

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11 Demagnetization energy

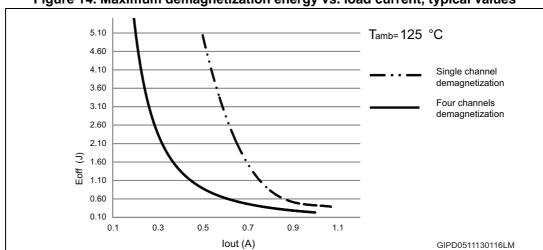


Figure 14. Maximum demagnetization energy vs. load current, typical values

12 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at:www.st.com. ECOPACK[®] is an ST trademark.

Table 10. PowerSSO-24 mechanical data

Oll	mm		
Symbol	Min.	Тур.	Max.
А	2.15		2.47
A2	2.15		2.40
a1	0		0.075
b	0.33		0.51
С	0.23		0.32
D	10.10		10.50
Е	7.4		7.6
е		0.8	
e3		8.8	
G			0.1
G1			0.06
Н	10.1		10.5
h			0.4
L	0.55		0.85
N			10deg
X	4.1		4.7
Y	6.5		7.1

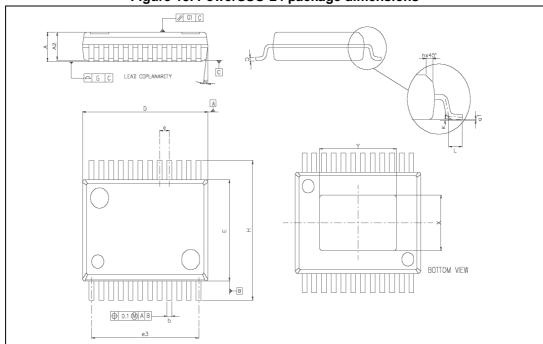
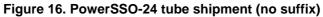


Figure 15. PowerSSO-24 package dimensions



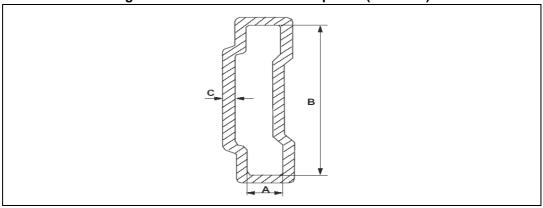


Table 11. PowerSSO-24 tube shipment

Base quantity	49
Bulk quantity	1225
Tube length (± 0.5)	532
Α	3.5
В	13.8
C (± 0.1)	0.6

Note: All dimensions are in mm.

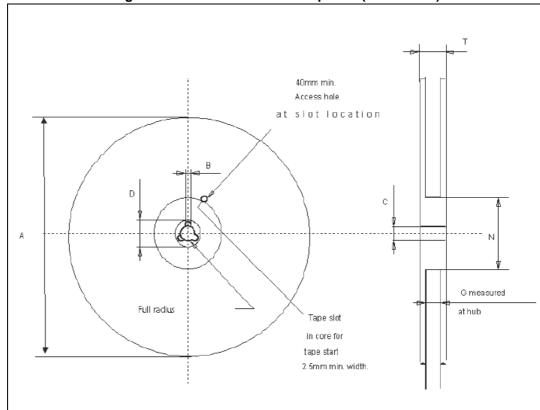


Figure 17. PowerSSO-24 reel shipment (suffix "TR")

Table 12. PowerSSO-24 reel dimensions

Base quantity	1000
Bulk quantity	1000
A (max.)	330
B (min.)	1.5
C (± 0.2)	13
F	20.2
G (2 ± 0)	24.4
N (min.)	100
T (max.)	30.4

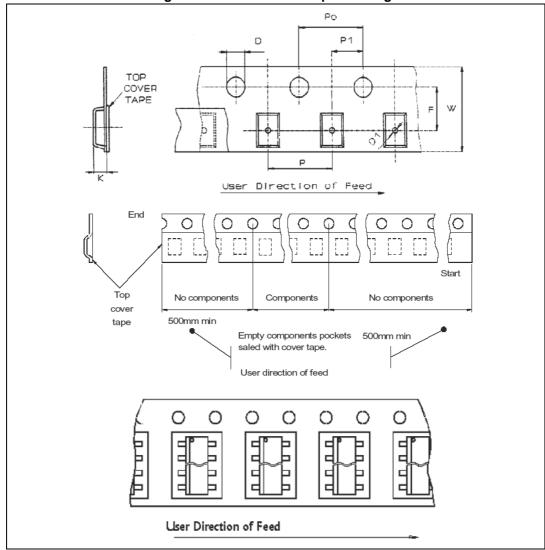


Figure 18. PowerSSO-24 tape drawings

Table 13. PowerSSO-24 tape dimensions

Tape width	W	24
Tape hole spacing	P0 (± 0.1)	4
Component spacing	Р	12
Hole diameter	D (± 0.05)	1.55
Hole diameter	D1 (min.)	1.5
Hole position	F (± 0.1)	11.5
Compartment depth	K (max.)	2.85
Hole spacing	P1 (± 0.1)	2

Note: According to the Electronic Industries Association (EIA) standard 481 rev. A, Feb 1986.

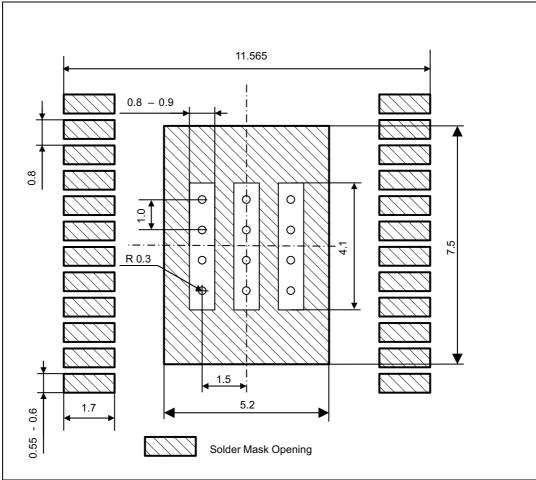


Figure 19. VNI4140K-32 suggested footprint

Note:

STMicroelectronics is not responsible for any PCB related issues. The footprint shown in the above figure is a suggestion which might not be in line to the customer PCB supplier design rules.

All dimensions are in mm.

Ordering information VNI4140K-32

13 Ordering information

Table 14. Ordering information

Order codes	Package	Packaging
VNI4140K-32	PowerSSO-24	Tube
VNI4140KTR-32	PowerSSO-24	Tape and reel

VNI4140K-32 Revision history

14 Revision history

Table 15. Document revision history

Date	Revision	Changes
12-Dec-2011	1	Initial release.
06-Feb-2012	2	Updated I _{lim} minimum value in <i>Table 8: Protection and diagnostic</i> . Inserted new feature: ESD according to IEC 61000-4-2 up to +/-25 KV, in cover page.
07-Mar-2012	3	Suggested footprint inserted. In <i>Table 5.</i> parameter I _{LGND} has been added.
25-Mar-2013	4	Updated I _{LIM} minimum value in <i>Table 8</i> . Minor text changes.
06-Nov-2013	5	Updated E _{AS} value in <i>Table 2: Absolute maximum ratings</i> . Added <i>Figure 14</i> .
11-Dec-2013	6	Updated Section 10.

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